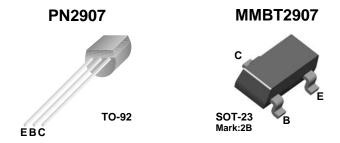


PN2907 / MMBT2907 PNP General-Purpose Transistor

Description

This device is designed for use with general-purpose amplifiers and switches requiring collector currents to 500 mA. Sourced from process 63.



Ordering Information

Part Number	Top Mark	Package	Packing Method
PN2907BU	PN2907	TO-92 3L	Bulk
MMBT29070-D87Z	2B	SOT-23 3L	Tape and Reel

Absolute Maximum Ratings(1),(2)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V _{CEO}	Collector-Emitter Voltage	-40	V
V_{CBO}	Collector-Base Voltage	-60	V
V _{EBO}	Emitter-Base Voltage	-5.0	V
I _C	Collector Current - Continuous	-800	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Notes:

- 1. These ratings are based on a maximum junction temperature of 150°C.
- 2. These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or lowduty cycle operations.

Thermal Characteristics

Values are at $T_A = 25$ °C unless otherwise noted.

Symbol Paramete	Parameter	Ma	Unit	
	raiametei	PN2907 ⁽³⁾	MMBT2907 ⁽⁴⁾	Uill
P _D	Total Device Dissipation	625	350	mW
	Derate Above 25°C	5.0	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

Notes:

- 3. PCB size: FR-4 76 x 114 x 1.57 mm³ (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.
- 4. Device mounted on FR-4 PCB 1.6. inch x 1.6 inch x 0.06 inch.

Electrical Characteristics

Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
Off Charac	cteristics	,			1
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage ⁽⁵⁾	$I_C = -10 \text{ mA}, I_B = 0$	-40		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = -10 \mu\text{A}, I_E = 0$	-60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = -10 \mu\text{A}, I_C = 0$	-5.0		V
I _{CEX}	Collector Cut-Off Current	V _{CE} = -30 V, V _{EB} = -0.5 V		-50	nA
I _{BL}	Base Cut-Off Current	V _{CE} = -30 V, V _{EB} = -0.5 V		-50	nA
	Collector Cut-Off Current	V _{CB} = -50 V, I _E = 0		-20	nA
I _{CBO}		V _{CB} = -50 V, I _E = 0, T _A = 150°C		-20	μΑ
On Charac	teristics ⁽⁵⁾				
		$V_{CE} = -10 \text{ V}, I_{C} = -0.1 \text{ mA}$	35		
		$V_{CE} = -10 \text{ V}, I_{C} = -1.0 \text{ mA}$	50		
h_{FE}	DC Current Gain	V _{CE} = -10 V, I _C = -10 mA	70		
		V _{CE} = -10 V, I _C = -150 mA	100	300	
		V _{CE} = -10 V, I _C = -500 mA	30		
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = -150 mA, I _B = -15 mA		-0.4	V
		I _C = -500 mA, I _B = -50 mA		-1.6	
\/ (4\)	Base-Emitter Saturation Voltage	I _C = -150 mA, I _B = -15 mA		-1.3	\/
V _{BE} (sat)		I _C = -500 mA, I _B = -50 mA		-2.6	V
Small Sigr	nal Characteristics				
C _{ob}	Output Capacitance	V _{CB} = -10 V, f = 1.0 MHz		8	pF
C _{ib}	Input Capacitance	V _{EB} = -2.0 V, f = 1.0 MHz		30	pF
h _{fe}	Small-Signal Current Gain	I _C = -50 mA, V _{CE} = -20 V, f = 100 MHz	2		
Switching	Characteristics				
t _{on}	Turn-On Time			45	ns
t _d	Delay Time	$V_{CC} = -30 \text{ V}, I_{C} = -150 \text{ mA},$ $I_{B1} = -15 \text{ mA}$		10	ns
t _r	Rise Time	יייי ייי		40	ns
t _{off}	Turn-Off Time			100	ns
t _s	Storage Time	$V_{CC} = -6.0 \text{ V, } I_{C} = -150 \text{ mA,}$ $I_{B1} = I_{B2} = -15\text{mA}$		80	ns
t _f	Fall Time	1 182 - 1911174		30	ns

Note:

5. Pulse test: pulse width \leq 300 μ s, duty cycle \leq 2.0%.

Physical Dimensions

TO-92 (Bulk)

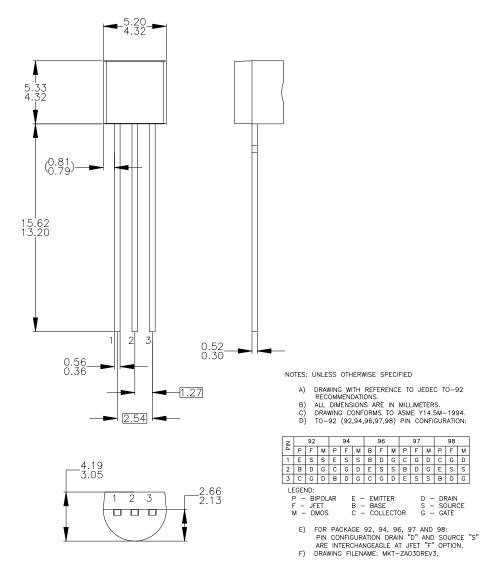
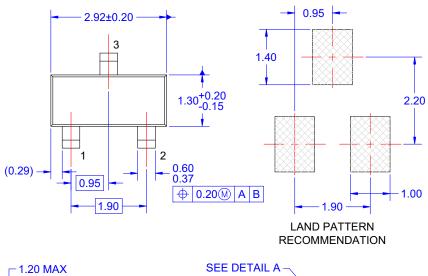


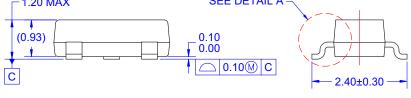
Figure 1. 3-LEAD, TO92, JEDEC TO-92 COMPLIANT STRAIGHT LEAD CONFIGURATION (OLD TO92AM3)

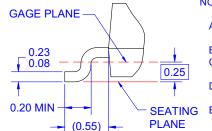
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Physical Dimensions (Continued)

SOT-23







- NOTES: UNLESS OTHERWISE SPECIFIED
 - A) REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H.
 - B) ALL DIMENSIONS ARE IN MILLIMETERS.
 - C) DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
 - D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994.
- E) DRAWING FILE NAME: MA03DREV10

DETAIL A
SCALE: 2X

Figure 2. 3-LEAD, SOT23, JEDEC TO-236, LOW PROFILE (ACTIVE)

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